

# Lecture #16

## OUTLINE

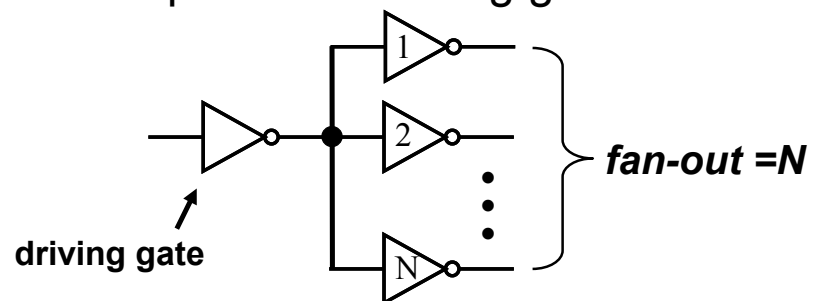
- Fan-out
- Propagation delay
- CMOS power consumption
- Timing Delay
- Sequential logic circuits

## Reading

- Rest of Chap 7
- Rabaey 5.1-5.3.2, 5.4-5.4.2, 5.5-5.5.2

## Fan-Out

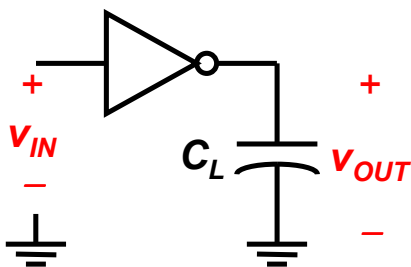
- Typically, the output of a logic gate is connected to the input(s) of one or more logic gates
- The **fan-out** is the number of gates that are connected to the output of the driving gate:



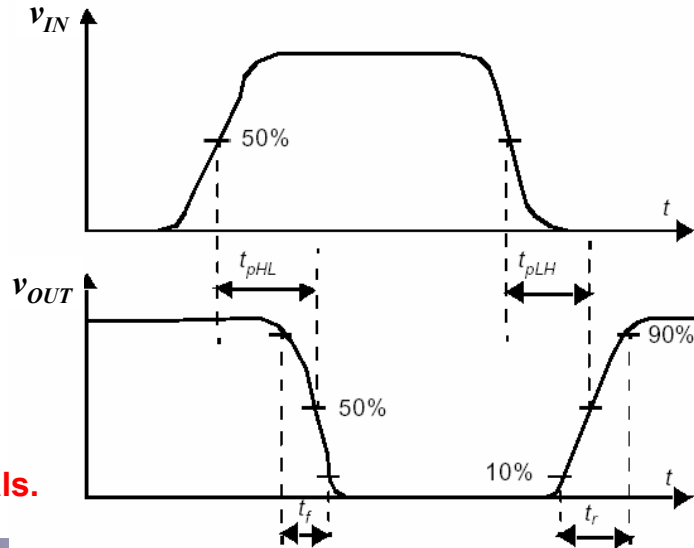
- Fanout leads to increased capacitive load on the driving gate, and therefore longer propagation delay
  - The input capacitances of the driven gates sum, and must be charged through the equivalent resistance of the driver

## Effect of Capacitive Loading

- When an input signal of a logic gate is changed, there is a **propagation delay** before the output of the logic gate changes. This is due to capacitive loading at the output.

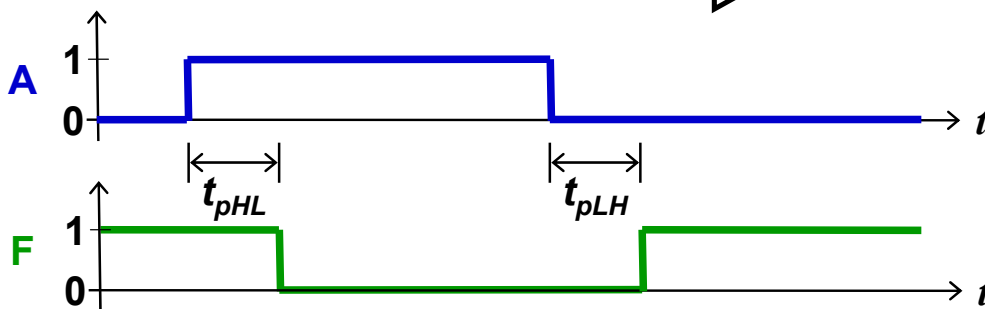
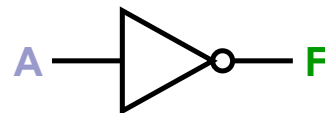


The propagation delay is measured between the 50% transition points of the input and output signals.



## Propagation Delay in Timing Diagrams

- To simplify the drawing of timing diagrams, we can **approximate the signal transitions to be abrupt** (though in reality they are exponential).



To further simplify timing analysis, we can define the propagation delay as  $t_p = (t_{pHL} + t_{pLH}) / 2$

# Examples of Propagation Delay

Product	CMOS technology generation	Clock frequency, $f$	Fan-out=4 inverter delay
Pentium II	0.25 $\mu\text{m}$	600 MHz	$\sim 100$ ps
Pentium III	0.18 $\mu\text{m}$	1.8 GHz	$\sim 40$ ps
Pentium IV	0.13 $\mu\text{m}$	3.2 GHz	$\sim 20$ ps

Typical clock periods:

- high-performance  $\mu\text{P}$ :  $\sim 15$  FO4 delays
- PlayStation 2: 60 FO4 delays

# Calculating the Propagation Delay

Model the MOSFET in the ON state as a resistive switch:

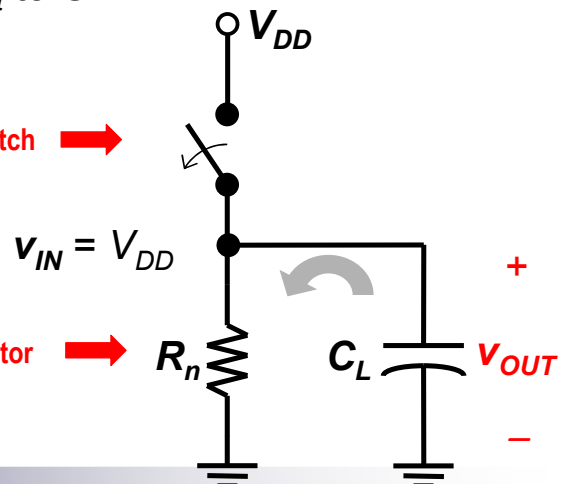
Case 1:  $V_{out}$  changing from High to Low  
(input signal changed from Low to High)

- NMOSFET(s) connect  $V_{out}$  to GND

$$t_{pHL} = 0.69 \times R_n C_L$$

Pull-up network is modeled as an open switch  $\rightarrow$

Pull-down network is modeled as a resistor  $\rightarrow$



## Calculating the Propagation Delay (cont'd)

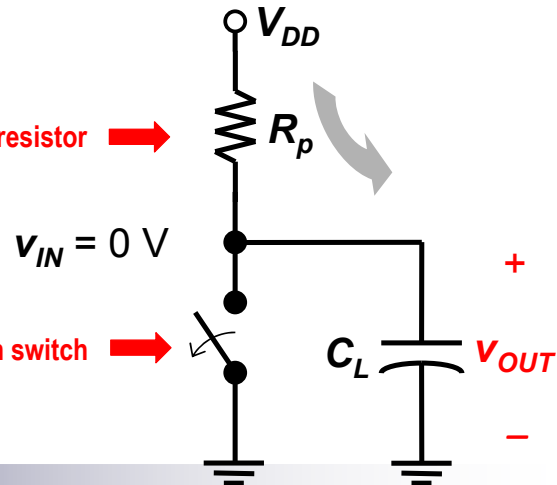
Case 2:  $V_{out}$  changing from Low to High  
(input signal changed from High to Low)

- PMOSFET(s) connect  $V_{out}$  to  $V_{DD}$

$$t_{pLH} = 0.69 \times R_p C_L$$

Pull-up network is modeled as a resistor  $\rightarrow$

Pull-down network is modeled as an open switch  $\rightarrow$



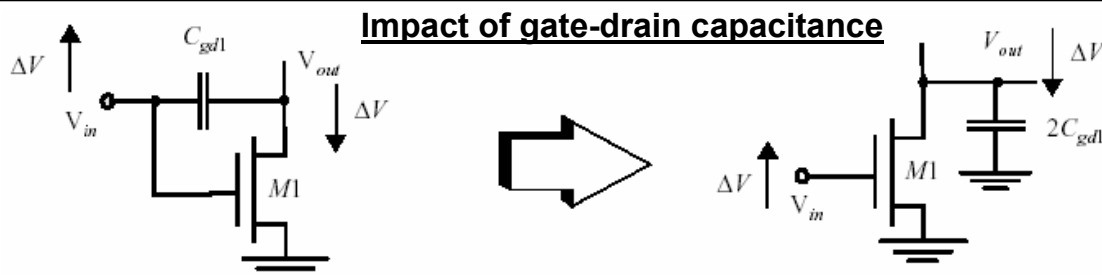
## Output Capacitance of a Logic Gate

- The output capacitance of a logic gate is comprised of several components:

“intrinsic capacitance”  $\rightarrow$ 

- pn-junction and gate-drain capacitance
- both NMOS and PMOS transistors

“extrinsic capacitance”  $\left\{ \begin{array}{l} \text{capacitance of connecting wires} \\ \text{input capacitances of the fan-out gates} \end{array} \right.$

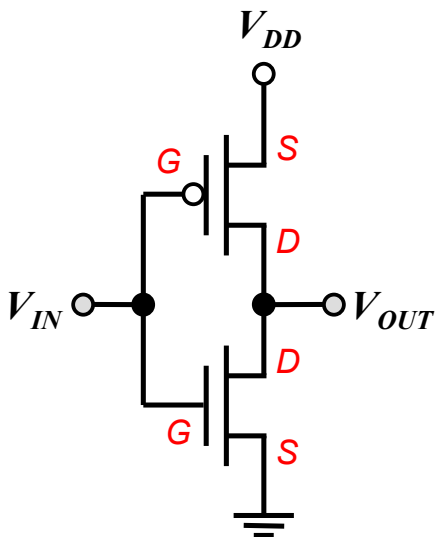


**Figure 5.14** The Miller effect—A capacitor experiencing identical but opposite voltage swings at both its terminals can be replaced by a capacitor to ground, whose value is two times the original value.

## Minimizing Propagation Delay

- A fast gate is built by
  1. **Keeping the output capacitance  $C_L$  small**
    - Minimize the area of drain pn junctions.
    - Lay out devices to minimize interconnect capacitance.
    - Avoid large fan-out.
  2. **Decreasing the equivalent resistance of the transistors**
    - Decrease  $L$
    - Increase  $W$ 
      - ... but this increases pn junction area and hence  $C_L$
  3. **Increasing  $V_{DD}$** 
    - trade-off with power consumption & reliability

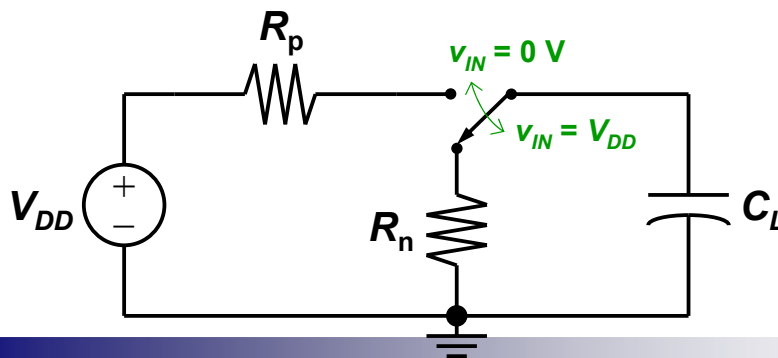
## Transistor Sizing for Performance



- Widening the transistors reduces resistance, but increases capacitance
- In order to have the on-state resistance of the PMOS transistor match that of the NMOS transistor (e.g. to achieve a symmetric voltage transfer curve), its  $W/L$  ratio must be larger by a factor of  $\sim 3$ . To achieve minimum propagation delay, however, **the optimum factor is  $\sim 2$ .**

## CMOS Energy Consumption (Review)

- The energy delivered by the voltage source in charging the load capacitance is  $C_L V_{DD}^2$ 
  - Half of this is stored in  $C_L$ ; the other half is absorbed by the resistance through which  $C_L$  is charged.
- In one complete cycle (charging and discharging), the total energy delivered by the voltage source is  $C_L V_{DD}^2$



## CMOS Power Consumption

- The total power consumed by a CMOS circuit is comprised of several components:
  1. **Dynamic power consumption due to charging and discharging capacitances\*:**

$$P_{dyn} = C_L V_{DD}^2 f_{0 \rightarrow 1} = C_{EFF} V_{DD}^2 f$$

$f_{0 \rightarrow 1}$  = frequency of 0→1 transitions (“switching activity”)

$f$  = clock rate (maximum possible event rate)

**Effective capacitance  $C_{EFF}$**  = average capacitance charged every clock cycle

**\* This is typically by far the dominant component!**

## CMOS Power Consumption (cont'd)

2. Dynamic power consumption due to direct-path currents during switching

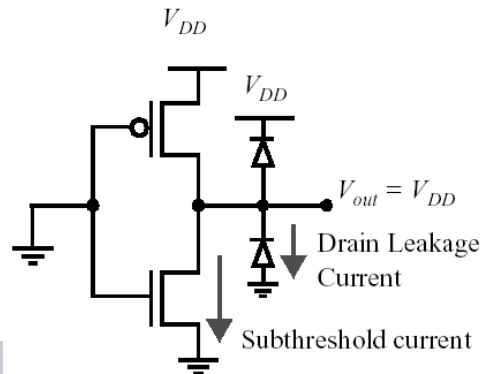
$$P_{dp} = C_{sc} V_{DD}^2 f$$

$C_{sc} = t_{sc} I_{peak} / V_{DD}$  is the equivalent capacitance charged every clock cycle due to "short-circuits" between  $V_{DD}$  &  $GND$

(typically <10% of total power consumption)

3. Static power consumption due to transistor leakage and pn-junction leakage

$$P_{stat} = I_{stat} V_{DD}$$



## Low-Power Design Techniques

1. Reduce  $V_{DD}$

→ quadratic effect on  $P_{dyn}$

Example: Reducing  $V_{DD}$  from 2.5 V to 1.25 V reduces power dissipation by factor of 4

- Lower bound is set by  $V_T$ :  $V_{DD}$  should be  $>2V_T$

2. Reduce load capacitance

→ Use minimum-sized transistors whenever possible

3. Reduce the switching activity

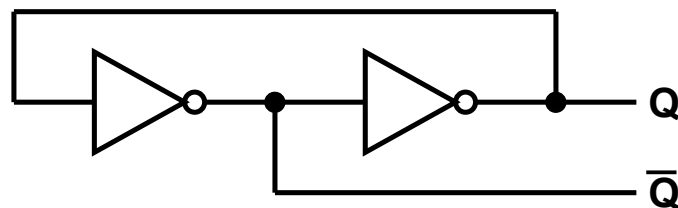
- involves design considerations at the architecture level (beyond the scope of this class!)

## NAND Gates vs. NOR Gates

- In order for a 2-input NAND gate to have the same pull-down delay ( $t_{pHL}$ ) as an inverter, the NMOS devices in the NAND gate must be made twice as wide.
    - This first-order analysis neglects the increase in capacitance which results from widening the transistors.
    - Note: The delay depends on the input signal pattern.
  - In order for a 2-input NOR gate to have the same pull-up delay ( $t_{pLH}$ ) as an inverter, the PMOS devices in the NOR gate must be made twice as wide.
    - Since hole mobility is lower than electron mobility (so that larger  $W/L$  ratios are needed for PMOS devices as compared with NMOS devices), stacking PMOS devices in series (as is done in a NOR gate) should be avoided as much as possible.
- **NAND gates are preferred for implementing logic!**

## Latches

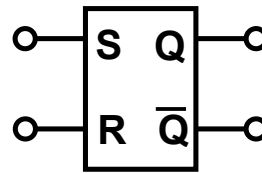
- One of the basic building blocks for sequential circuits is the ***latches***:
  - 2 stable operating states → stores 1 bit of info.
  - A simple latch can be constructed using two inverters:





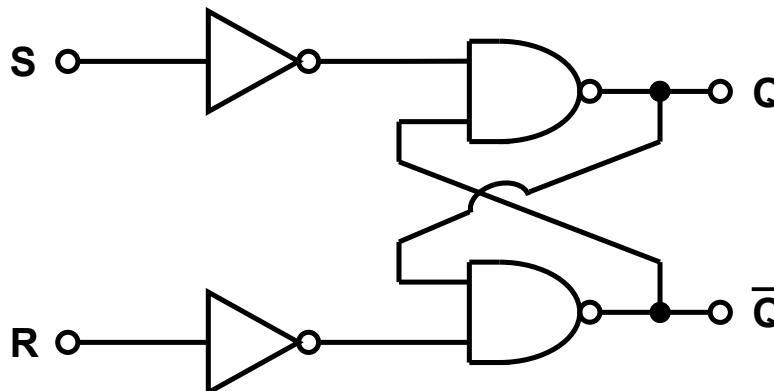
# The S-R (“Set”-“Reset”) Latch

S-R Latch Symbol:



- Rule 1:
  - If  $S = 0$  and  $R = 0$ ,  $Q$  does not change.
- Rule 2:
  - If  $S = 0$  and  $R = 1$ , then  $Q = 0$
- Rule 3:
  - If  $S = 1$  and  $R = 0$ , then  $Q = 1$
- Rule 4:
  - $S = 1$  and  $R = 1$  should never occur.

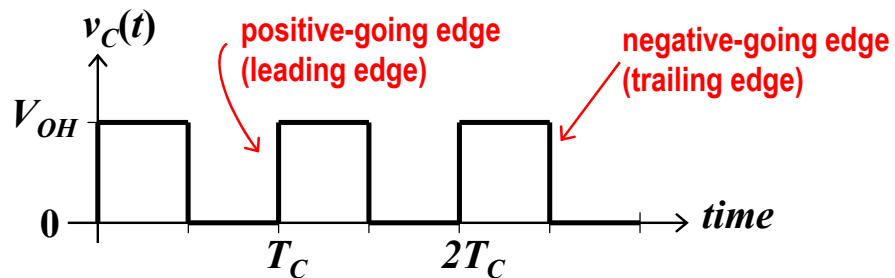
# Realization of the S-R Latch



R	S	$Q_n$
0	0	$Q_{n-1}$
0	1	1
1	0	0
1	1	(not allowed)

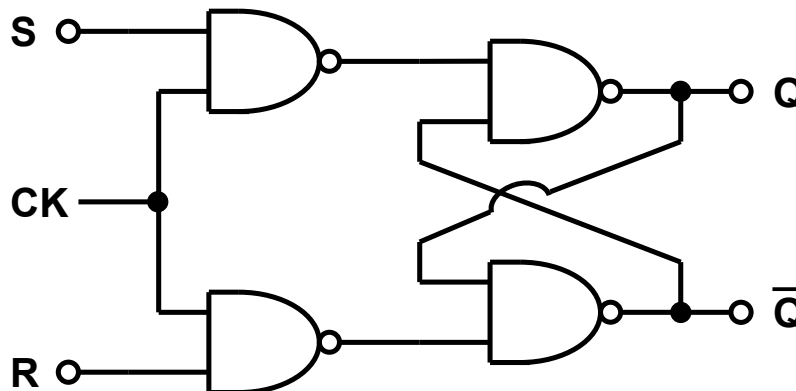
## Clock Signals

- Often, the operation of a sequential circuit is synchronized by a **clock signal** :



- The clock signal regulates when the circuits respond to new inputs, so that operations occur in proper sequence.
- Sequential circuits that are regulated by a clock signal are said to be **synchronous**.

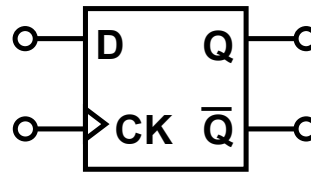
## Clocked S-R Latch



- When **CK = 0**, the value of **Q** does not change
- When **CK = 1**, the circuit acts like an ordinary S-R latch

# The D (“Delay”) Flip-Flop

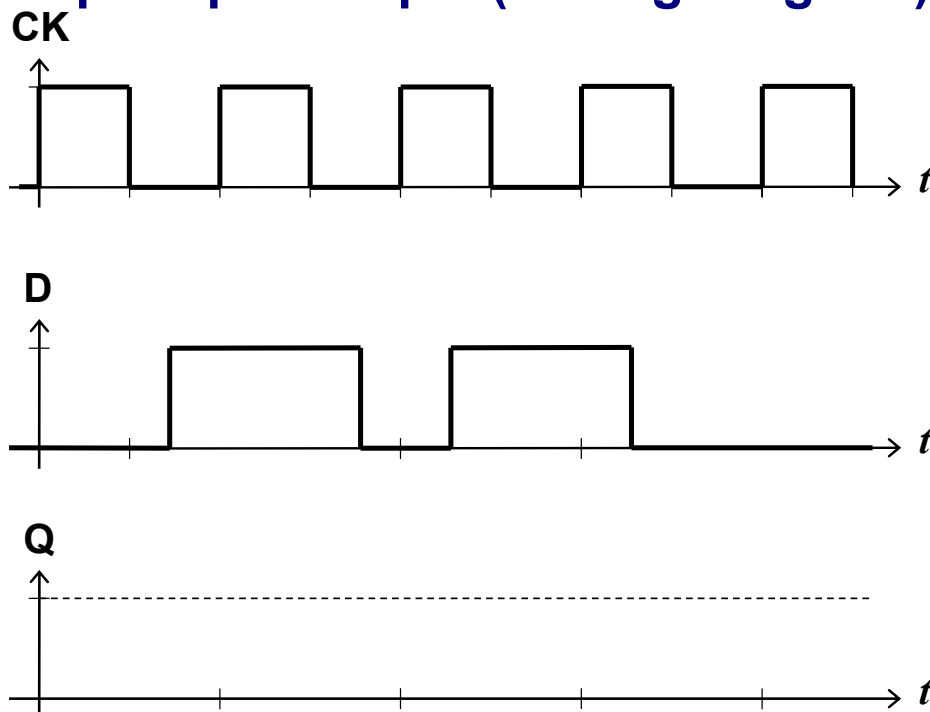
D Flip-Flop Symbol:



- **Q** changes only when the clock signal **CK** makes a positive transition.

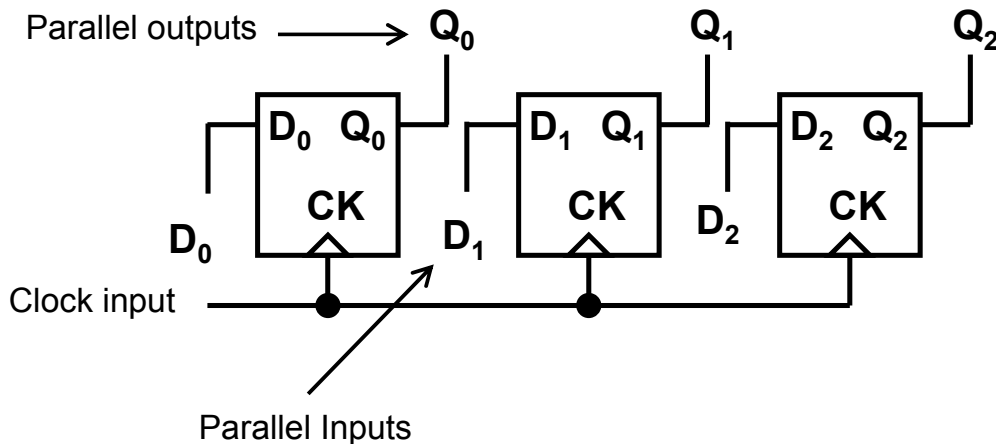
CK	D	$Q_n$
0	x	$Q_{n-1}$
1	x	$Q_{n-1}$
↑	0	0
↑	1	1

## D Flip-Flop Example (Timing Diagram)



## Registers

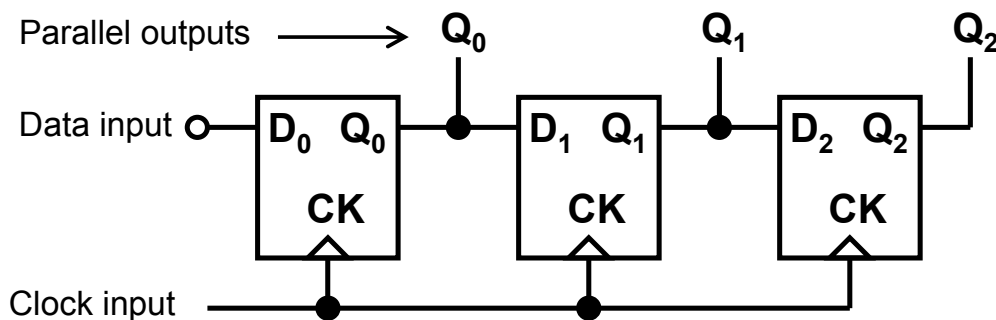
- A **register** is an array of flip-flops that is used to store.



## Shift Registers

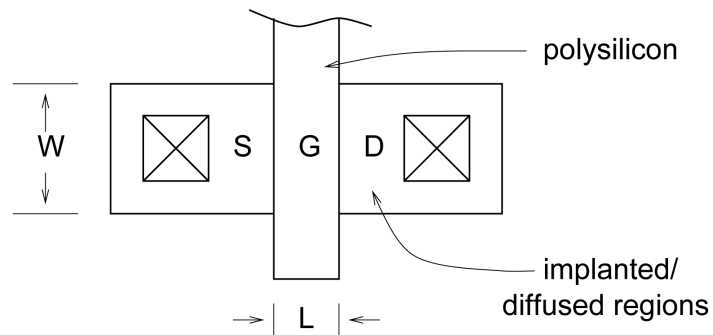
- A **register** can be used to manipulate the bits of a digital word.

Example: Serial-In, Parallel-Out Shift Register

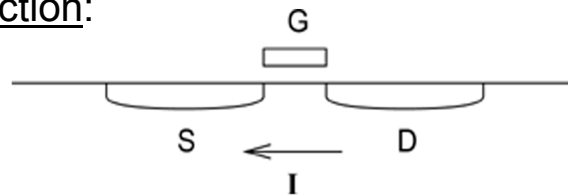


# MOSFET Layout and Cross-Section

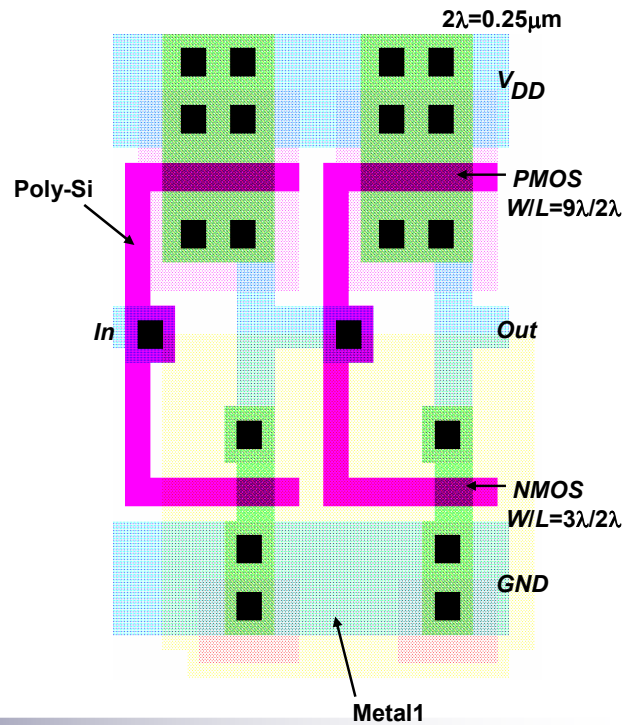
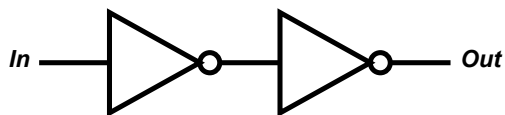
Top View:



Cross Section:



# Inverter Layout





## Conclusion (Logic Circuits)

- Complex combinational logic functions can be achieved simply by interconnecting NAND gates (or NOR gates).
- Logic gates can be interconnected to form flip-flops.
- Interconnections of flip-flops form registers.
- A complex digital system such as a computer consists of many gates, flip-flops, and registers. Thus, logic gates are the basic building blocks for complex digital systems.